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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	2566
Number of Logic Elements/Cells	25660
Total RAM Bits	1944576
Number of I/O	597
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	780-BBGA
Supplier Device Package	780-FBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s25f780c5

I.S. EN ISO 9001

2. Stratix Architecture

Functional Description

Stratix® devices contain a two-dimensional row- and column-based architecture to implement custom logic. A series of column and row interconnects of varying length and speed provide signal interconnects between logic array blocks (LABs), memory block structures, and DSP blocks.

The logic array consists of LABs, with 10 logic elements (LEs) in each LAB. An LE is a small unit of logic providing efficient implementation of user logic functions. LABs are grouped into rows and columns across the device.

M512 RAM blocks are simple dual-port memory blocks with 512 bits plus parity (576 bits). These blocks provide dedicated simple dual-port or single-port memory up to 18-bits wide at up to 318 MHz. M512 blocks are grouped into columns across the device in between certain LABs.

M4K RAM blocks are true dual-port memory blocks with 4K bits plus parity (4,608 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 36-bits wide at up to 291 MHz. These blocks are grouped into columns across the device in between certain LABs.

M-RAM blocks are true dual-port memory blocks with 512K bits plus parity (589,824 bits). These blocks provide dedicated true dual-port, simple dual-port, or single-port memory up to 144-bits wide at up to 269 MHz. Several M-RAM blocks are located individually or in pairs within the device's logic array.

Digital signal processing (DSP) blocks can implement up to either eight full-precision 9 × 9-bit multipliers, four full-precision 18 × 18-bit multipliers, or one full-precision 36 × 36-bit multiplier with add or subtract features. These blocks also contain 18-bit input shift registers for digital signal processing applications, including FIR and infinite impulse response (IIR) filters. DSP blocks are grouped into two columns in each device.

Each Stratix device I/O pin is fed by an I/O element (IOE) located at the end of LAB rows and columns around the periphery of the device. I/O pins support numerous single-ended and differential I/O standards. Each IOE contains a bidirectional I/O buffer and six registers for registering input, output, and output-enable signals. When used with

dedicated clocks, these registers provide exceptional performance and interface support with external memory devices such as DDR SDRAM, FCRAM, ZBT, and QDR SRAM devices.

High-speed serial interface channels support transfers at up to 840 Mbps using LVDS, LVPECL, 3.3-V PCML, or HyperTransport technology I/O standards.

Figure 2–1 shows an overview of the Stratix device.
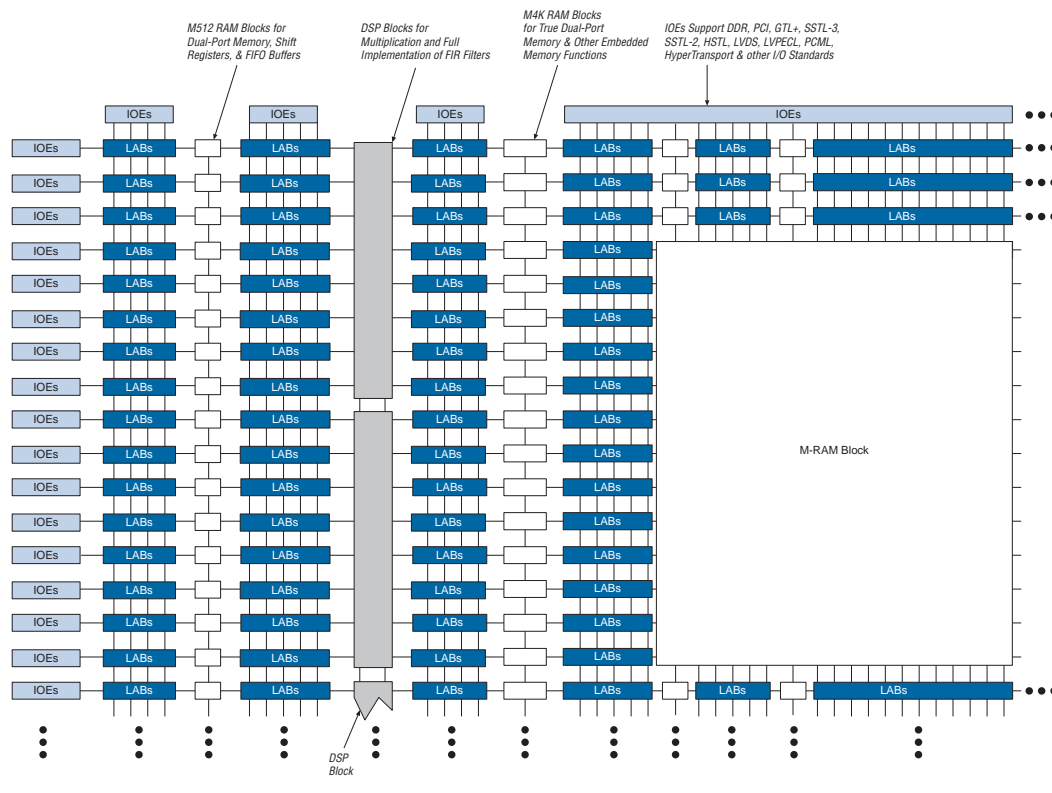
Figure 2–1. Stratix Block Diagram

Figure 2–2. Stratix LAB Structure
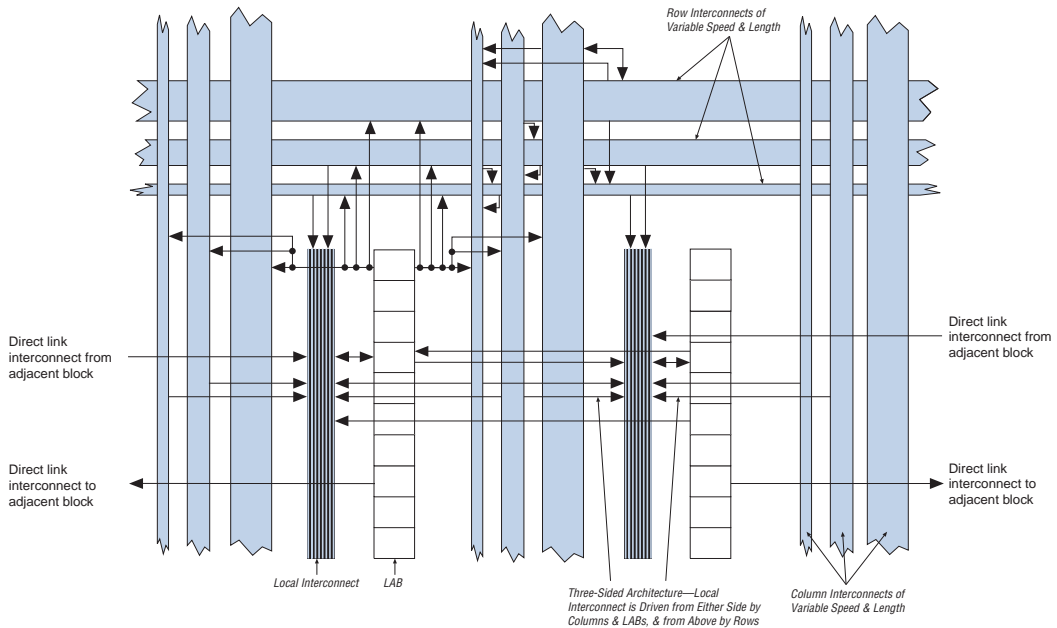
LAB Interconnects

The LAB local interconnect can drive LEs within the same LAB. The LAB local interconnect is driven by column and row interconnects and LE outputs within the same LAB. Neighboring LABs, M512 RAM blocks, M4K RAM blocks, or DSP blocks from the left and right can also drive an LAB's local interconnect through the direct link connection. The direct link connection feature minimizes the use of row and column interconnects, providing higher performance and flexibility. Each LE can drive 30 other LEs through fast local and direct link interconnects. Figure 2–3 shows the direct link connection.

asynchronous load, and clear signals. An asynchronous clear signal takes precedence if both signals are asserted simultaneously. Each LAB supports up to two clears and one preset signal.

In addition to the clear and preset ports, Stratix devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. An option set before compilation in the Quartus II software controls this pin. This chip-wide reset overrides all other control signals.

MultiTrack Interconnect

In the Stratix architecture, connections between LEs, TriMatrix memory, DSP blocks, and device I/O pins are provided by the MultiTrack interconnect structure with DirectDrive™ technology. The MultiTrack interconnect consists of continuous, performance-optimized routing lines of different lengths and speeds used for inter- and intra-design block connectivity. The Quartus II Compiler automatically places critical design paths on faster interconnects to improve design performance.

DirectDrive technology is a deterministic routing technology that ensures identical routing resource usage for any function regardless of placement within the device. The MultiTrack interconnect and DirectDrive technology simplify the integration stage of block-based designing by eliminating the re-optimization cycles that typically follow design changes and additions.

The MultiTrack interconnect consists of row and column interconnects that span fixed distances. A routing structure with fixed length resources for all devices allows predictable and repeatable performance when migrating through different device densities. Dedicated row interconnects route signals to and from LABs, DSP blocks, and TriMatrix memory within the same row. These row resources include:

- Direct link interconnects between LABs and adjacent blocks.
- R4 interconnects traversing four blocks to the right or left.
- R8 interconnects traversing eight blocks to the right or left.
- R24 row interconnects for high-speed access across the length of the device.

The direct link interconnect allows an LAB, DSP block, or TriMatrix memory block to drive into the local interconnect of its left and right neighbors and then back into itself. Only one side of a M-RAM block interfaces with direct link and row interconnects. This provides fast communication between adjacent LABs and/or blocks without using row interconnect resources.

The R4 interconnects span four LABs, three LABs and one M512 RAM block, two LABs and one M4K RAM block, or two LABs and one DSP block to the right or left of a source LAB. These resources are used for fast

row connections in a four-LAB region. Every LAB has its own set of R4 interconnects to drive either left or right. Figure 2–9 shows R4 interconnect connections from an LAB. R4 interconnects can drive and be driven by DSP blocks and RAM blocks and horizontal IOEs. For LAB interfacing, a primary LAB or LAB neighbor can drive a given R4 interconnect. For R4 interconnects that drive to the right, the primary LAB and right neighbor can drive on to the interconnect. For R4 interconnects that drive to the left, the primary LAB and its left neighbor can drive on to the interconnect. R4 interconnects can drive other R4 interconnects to extend the range of LABs they can drive. R4 interconnects can also drive C4 and C16 interconnects for connections from one row to another. Additionally, R4 interconnects can drive R24 interconnects.

Figure 2–9. R4 Interconnect Connections
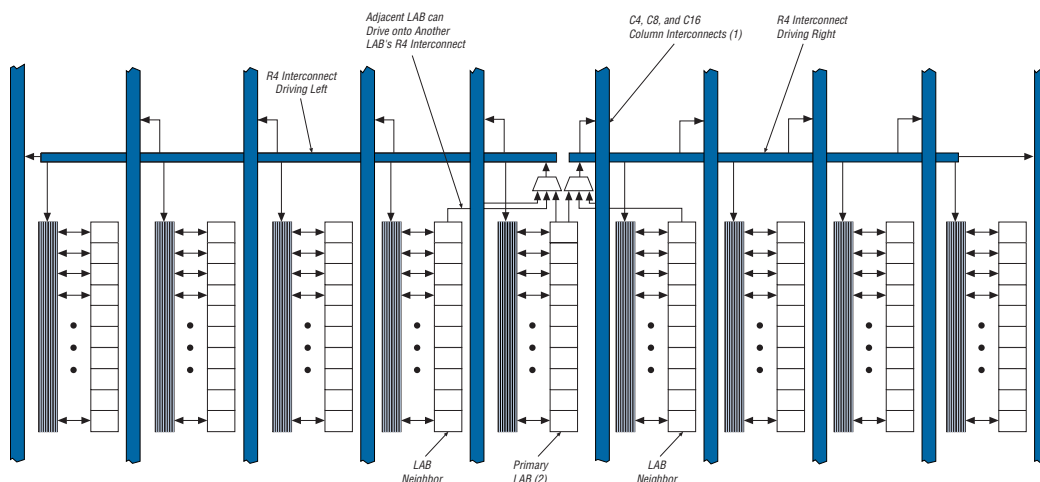
Notes to Figure 2–9:
(1)   C4 interconnects can drive R4 interconnects.
(2)   This pattern is repeated for every LAB in the LAB row.

The R8 interconnects span eight LABs, M512 or M4K RAM blocks, or DSP blocks to the right or left from a source LAB. These resources are used for fast row connections in an eight-LAB region. Every LAB has its own set of R8 interconnects to drive either left or right. R8 interconnect connections between LABs in a row are similar to the R4 connections shown in Figure 2–9, with the exception that they connect to eight LABs to the right or left, not four. Like R4 interconnects, R8 interconnects can drive and be driven by all types of architecture blocks. R8 interconnects

Figure 2–25. Input/Output Clock Mode in True Dual-Port Mode Notes (1), (2)
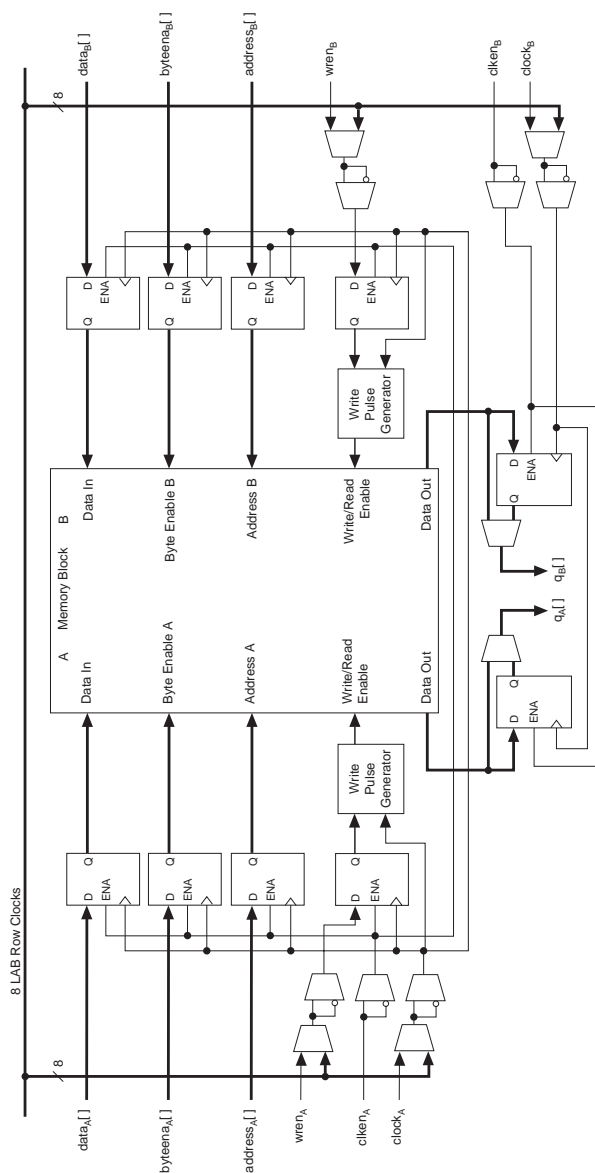
Notes to Figure 2–25:
(1)   All registers shown have asynchronous clear ports.
(2)   Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

Read/Write Clock Mode

The memory blocks implement read/write clock mode for simple dual-port memory. You can use up to two clocks in this mode. The write clock controls the block's data inputs, wraddress, and wren. The read clock controls the data output, rdaddress, and rden. The memory blocks support independent clock enables for each clock and asynchronous clear signals for the read- and write-side registers. Figure 2–27 shows a memory block in read/write clock mode.

Figure 2–61. Column I/O Block Connection to the Interconnect

Notes to Figure 2–61:
(1) The 16 control signals are composed of four output enables `io_boe[3..0]`, four clock enables `io_bce[3..0]`, four clocks `io_bclk[3..0]`, and four clear signals `io_bclr[3..0]`.
(2) The 42 data and control signals consist of 12 data out lines; six lines each for DDR applications `io_dataouta[5..0]` and `io_dataoutb[5..0]`, six output enables `io_coe[5..0]`, six input clock enables `io_cce_in[5..0]`, six output clock enables `io_cce_out[5..0]`, six clocks `io_cclk[5..0]`, and six clear signals `io_cclr[5..0]`.

Figure 2–70. Stratix I/O Banks Notes (1), (2), (3)
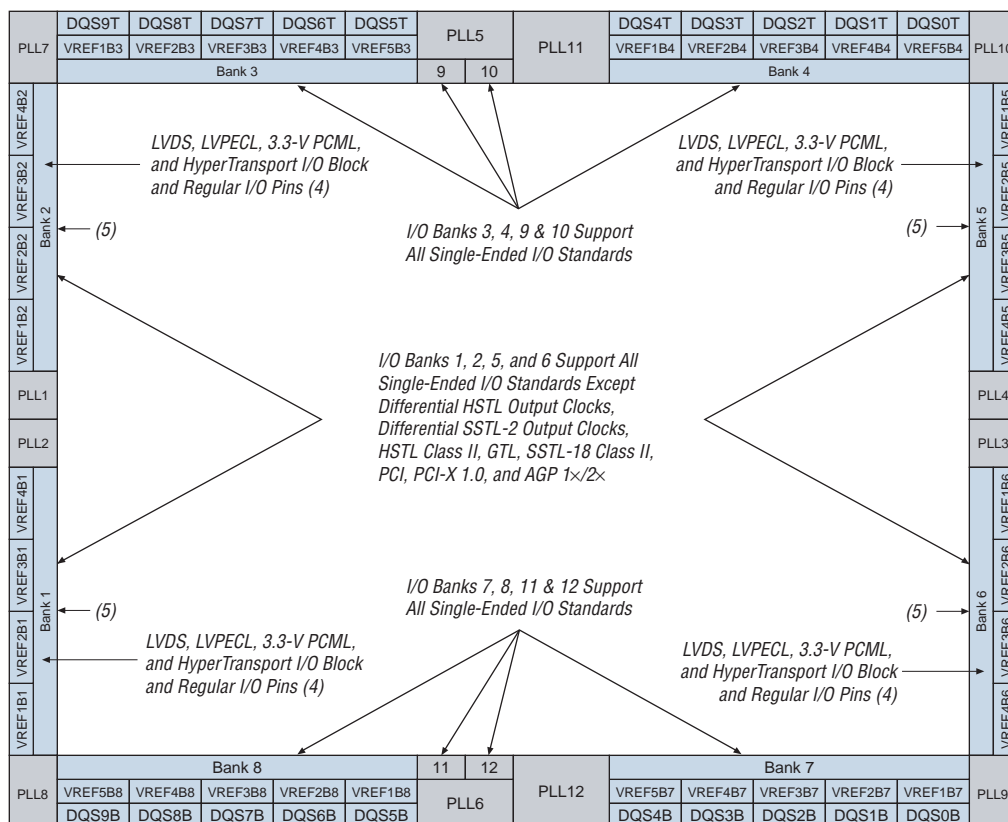
Notes to Figure 2–70:
(1) Figure 2–70 is a top view of the silicon die. This will correspond to a top-down view for non-flip-chip packages, but will be a reverse view for flip-chip packages.
(2) Figure 2–70 is a graphic representation only. See the device pin-outs on the web (**www.altera.com**) and the Quartus II software for exact locations.
(3) Banks 9 through 12 are enhanced PLL external clock output banks.
(4) If the high-speed differential I/O pins are not used for high-speed differential signaling, they can support all of the I/O standards except HSTL Class I and II, GTL, SSTL-18 Class II, PCI, PCI-X 1.0, and AGP 1× /2× .
(5) For guidelines for placing single-ended I/O pads next to differential I/O pads, see the *Selectable I/O Standards in Stratix and Stratix GX Devices* chapter in the *Stratix Device Handbook, Volume 2.*

Table 2–32 shows I/O standard support for each I/O bank.

Table 2–32. I/O Support by Bank (Part 1 of 2)			
I/O Standard	Top & Bottom Banks (3, 4, 7 & 8)	Left & Right Banks (1, 2, 5 & 6)	Enhanced PLL External Clock Output Banks (9, 10, 11 & 12)
LVTTL	✓	✓	✓
LVCMOS	✓	✓	✓
2.5 V	✓	✓	✓
1.8 V	✓	✓	✓
1.5 V	✓	✓	✓
3.3-V PCI	✓		✓
3.3-V PCI-X 1.0	✓		✓
LVPECL		✓	✓
3.3-V PCML		✓	✓
LVDS		✓	✓
HyperTransport technology		✓	✓
Differential HSTL (clock inputs)	✓	✓	
Differential HSTL (clock outputs)			✓
Differential SSTL (clock outputs)			✓
3.3-V GTL	✓		✓
3.3-V GTL+	✓	✓	✓
1.5-V HSTL Class I	✓	✓	✓
1.5-V HSTL Class II	✓		✓
1.8-V HSTL Class I	✓	✓	✓
1.8-V HSTL Class II	✓		✓
SSTL-18 Class I	✓	✓	✓
SSTL-18 Class II	✓		✓
SSTL-2 Class I	✓	✓	✓
SSTL-2 Class II	✓	✓	✓
SSTL-3 Class I	✓	✓	✓

The Stratix device instruction register length is 10 bits and the USERCODE register length is 32 bits. Tables 3–2 and 3–3 show the boundary-scan register length and device IDCODE information for Stratix devices.

Table 3–2. Stratix Boundary-Scan Register Length	
Device	**Boundary-Scan Register Length**
EP1S10	1,317
EP1S20	1,797
EP1S25	2,157
EP1S30	2,253
EP1S40	2,529
EP1S60	3,129
EP1S80	3,777

Table 3–3. 32-Bit Stratix Device IDCODE				
Device	**IDCODE (32 Bits)** *(1)*			
	Version (4 Bits)	**Part Number (16 Bits)**	**Manufacturer Identity (11 Bits)**	**LSB (1 Bit)** *(2)*
EP1S10	0000	0010 0000 0000 0001	000 0110 1110	1
EP1S20	0000	0010 0000 0000 0010	000 0110 1110	1
EP1S25	0000	0010 0000 0000 0011	000 0110 1110	1
EP1S30	0000	0010 0000 0000 0100	000 0110 1110	1
EP1S40	0000	0010 0000 0000 0101	000 0110 1110	1
EP1S60	0000	0010 0000 0000 0110	000 0110 1110	1
EP1S80	0000	0010 0000 0000 0111	000 0110 1110	1

Notes to Tables 3–2 and 3–3:
(1)   The most significant bit (MSB) is on the left.
(2)   The IDCODE's least significant bit (LSB) is always 1.

Table 4–2. Stratix Device Recommended Operating Conditions (Part 2 of 2)					
Symbol	**Parameter**	**Conditions**	**Minimum**	**Maximum**	**Unit**
V$_{CCIO}$	Supply voltage for output buffers, 3.3-V operation	*(4)*, *(5)*	3.00 (3.135)	3.60 (3.465)	V
	Supply voltage for output buffers, 2.5-V operation	*(4)*	2.375	2.625	V
	Supply voltage for output buffers, 1.8-V operation	*(4)*	1.71	1.89	V
	Supply voltage for output buffers, 1.5-V operation	*(4)*	1.4	1.6	V
V$_I$	Input voltage	*(3)*, *(6)*	−0.5	4.0	V
V$_O$	Output voltage		0	V$_{CCIO}$	V
T$_J$	Operating junction temperature	For commercial use	0	85	°C
		For industrial use	−40	100	°C

Table 4–3. Stratix Device DC Operating Conditions Note (7) (Part 1 of 2)						
Symbol	**Parameter**	**Conditions**	**Minimum**	**Typical**	**Maximum**	**Unit**
I$_I$	Input pin leakage current	V$_I$ = V$_{CCIOmax}$ to 0 V *(8)*	−10		10	μA
I$_{OZ}$	Tri-stated I/O pin leakage current	V$_O$ = V$_{CCIOmax}$ to 0 V *(8)*	−10		10	μA
I$_{CC0}$	V$_{CC}$ supply current (standby) (All memory blocks in power-down mode)	V$_I$ = ground, no load, no toggling inputs				mA
		EP1S10. V$_I$ = ground, no load, no toggling inputs		37		mA
		EP1S20. V$_I$ = ground, no load, no toggling inputs		65		mA
		EP1S25. V$_I$ = ground, no load, no toggling inputs		90		mA
		EP1S30. V$_I$ = ground, no load, no toggling inputs		114		mA
		EP1S40. V$_I$ = ground, no load, no toggling inputs		145		mA
		EP1S60. V$_I$ = ground, no load, no toggling inputs		200		mA
		EP1S80. V$_I$ = ground, no load, no toggling inputs		277		mA

device. Decoupling capacitors were not used in this measurement. To factor in the current for decoupling capacitors, sum up the current for each capacitor using the following equation:

$$I = C \, (dV/dt)$$

If the regulator or power supply minimum output current is more than the Stratix device requires, then the device may consume more current than the maximum current listed in Table 4–34. However, the device does not require any more current to successfully power up than what is listed in Table 4–34.

| Table 4–34. Stratix Power-Up Current (I_{CCINT}) Requirements Note (1)			
Device	**Power-Up Current Requirement**		**Unit**
	Typical	**Maximum**	
EP1S10	250	700	mA
EP1S20	400	1,200	mA
EP1S25	500	1,500	mA
EP1S30	550	1,900	mA
EP1S40	650	2,300	mA
EP1S60	800	2,600	mA
EP1S80	1,000	3,000	mA

Note to Table 4–34:

(1) The maximum test conditions are for 0° C and typical test conditions are for 40° C.

The exact amount of current consumed varies according to the process, temperature, and power ramp rate. Stratix devices typically require less current during power up than shown in Table 4–34. The user-mode current during device operation is generally higher than the power-up current.

The duration of the I_{CCINT} power-up requirement depends on the V_{CCINT} voltage supply rise time. The power-up current consumption drops when the V_{CCINT} supply reaches approximately 0.75 V.

Figure 4–3 shows the TriMatrix memory waveforms for the M512, M4K, and M-RAM timing parameters shown in Tables 4–40 through 4–42.

Figure 4–3. Dual-Port RAM Timing Microparameter Waveform
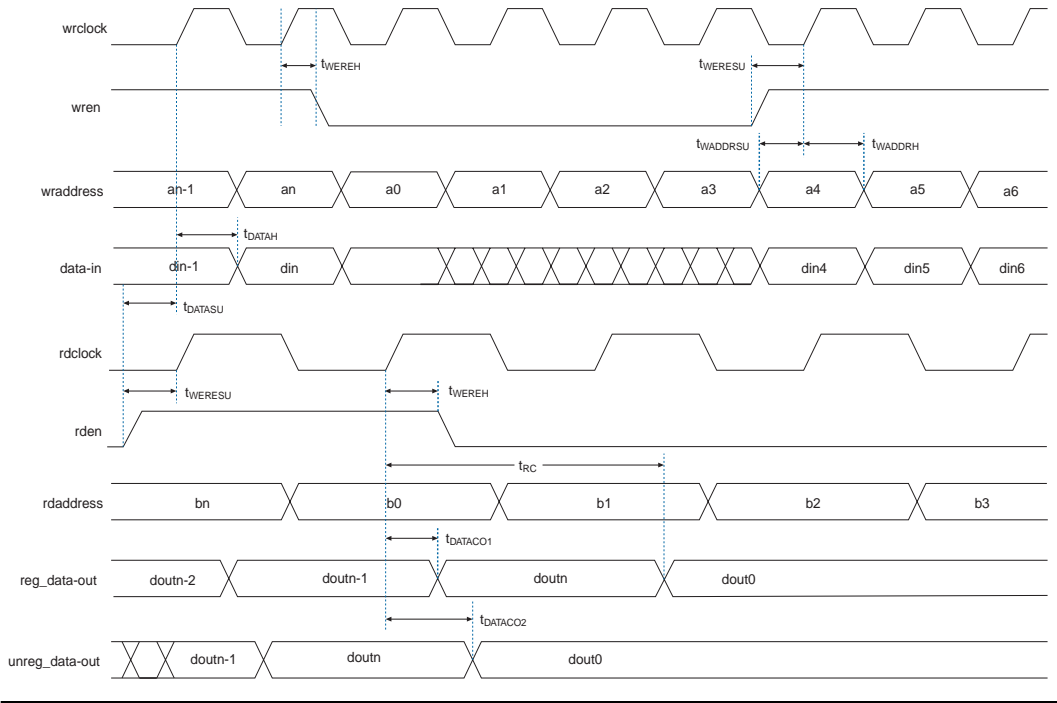
Internal timing parameters are specified on a speed grade basis independent of device density. Tables 4–44 through 4–50 show the internal timing microparameters for LEs, IOEs, TriMatrix memory structures, DSP blocks, and MultiTrack interconnects.

Table 4–43. Routing Delay Internal Timing Microparameter Descriptions (Part 1 of 2)

Symbol	Parameter
t_{R4}	Delay for an R4 line with average loading; covers a distance of four LAB columns.
t_{R8}	Delay for an R8 line with average loading; covers a distance of eight LAB columns.
t_{R24}	Delay for an R24 line with average loading; covers a distance of 24 LAB columns.

Figure 4–6 shows the case where four IOE registers are located in two different I/O banks.

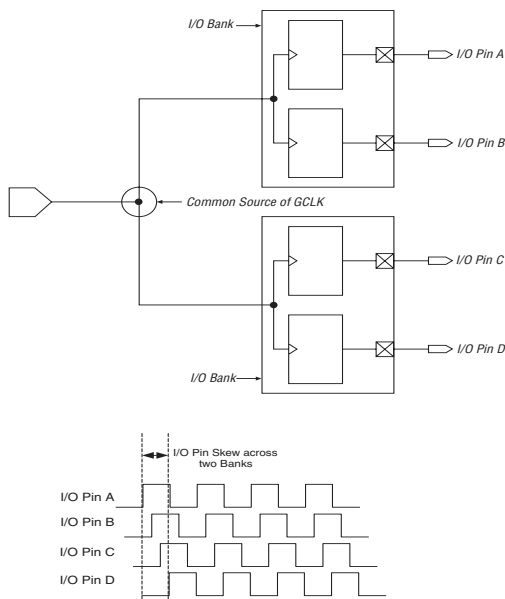*Figure 4–6. I/O Skew Across Two I/O Banks*

Table 4–97 defines the timing parameters used to define the timing for horizontal I/O pins (side banks 1, 2, 5, 6) and vertical I/O pins (top and bottom banks 3, 4, 7, 8). The timing parameters define the skew within an I/O bank, across two neighboring I/O banks on the same side of the device, across all horizontal I/O banks, across all vertical I/O banks, and the skew for the overall device.

Table 4–97. Output Pin Timing Skew Definitions   (Part 1 of 2)

Symbol	Definition
t_{SB_HIO}	Row I/O (HIO) within one I/O bank *(1)*
t_{SB_VIO}	Column I/O (VIO) within one I/O bank *(1)*
t_{SS_HIO}	Row I/O (HIO) same side of the device, across two banks *(2)*
t_{SS_VIO}	Column I/O (VIO) same side of the device, across two banks *(2)*

Table 4–97. Output Pin Timing Skew Definitions   (Part 2 of 2)

Symbol	Definition
t_{LR_HIO}	Across all HIO banks (1, 2, 5, 6); across four similar type I/O banks
t_{TB_VIO}	Across all VIO banks (3, 4, 7, 8); across four similar type I/O banks
$t_{OVERALL}$	Output timing skew for all I/O pins on the device.

Notes to Table 4–97:
(1) See Figure 4–5 on page 4–57.
(2) See Figure 4–6 on page 4–58.

Table 4–98 shows the I/O skews when using the same global or regional clock to feed IOE registers in I/O banks around each device. These values can be used for calculating the timing budget on the output (write) side of a memory interface. These values already factor in the package skew.

Table 4–98. Output Skew for Stratix by Device Density

Symbol	Skew (ps) (1)		
	EP1S10 to EP1S30	EP1S40	EP1S60 & EP1S80
t_{SB_HIO}	90	290	500
t_{SB_VIO}	160	290	500
t_{SS_HIO}	90	460	600
t_{SS_VIO}	180	520	630
t_{LR_HIO}	150	490	600
t_{TB_VIO}	190	580	670
$t_{OVERALL}$	430	630	880

Note to Table 4–98:
(1) The skew numbers in Table 4–98 account for worst case package skews.

Table 4–120. Stratix Maximum Output Clock Rate for PLL[5, 6, 11, 12] Pins in Flip-Chip Packages (Part 2 of 2)

I/O Standard	-5 Speed Grade	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
SSTL-2 Class II *(3)*	200	200	167	167	MHz
SSTL-2 Class II *(4)*	200	200	167	167	MHz
SSTL-2 Class II *(5)*	150	134	134	134	MHz
SSTL-18 Class I	150	133	133	133	MHz
SSTL-18 Class II	150	133	133	133	MHz
1.5-V HSTL Class I	250	225	200	200	MHz
1.5-V HSTL Class II	225	200	200	200	MHz
1.8-V HSTL Class I	250	225	200	200	MHz
1.8-V HSTL Class II	225	200	200	200	MHz
3.3-V PCI	350	300	250	250	MHz
3.3-V PCI-X 1.0	350	300	250	250	MHz
Compact PCI	350	300	250	250	MHz
AGP 1×	350	300	250	250	MHz
AGP 2×	350	300	250	250	MHz
CTT	200	200	200	200	MHz
Differential 1.5-V HSTL C1	225	200	200	200	MHz
Differential 1.8-V HSTL Class I	250	225	200	200	MHz
Differential 1.8-V HSTL Class II	225	200	200	200	MHz
Differential SSTL-2 *(6)*	200	200	167	167	MHz
LVPECL *(2)*	500	500	500	500	MHz
PCML *(2)*	350	350	350	350	MHz
LVDS *(2)*	500	500	500	500	MHz
HyperTransport technology *(2)*	350	350	350	350	MHz

Table 4–123. Stratix Maximum Output Clock Rate (Using I/O Pins) for PLL[1, 2, 3, 4] Pins in Wire-Bond Packages (Part 2 of 2)

I/O Standard	-6 Speed Grade	-7 Speed Grade	-8 Speed Grade	Unit
LVDS *(2)*	400	311	311	MHz
HyperTransport technology *(2)*	420	400	400	MHz

Notes to Tables 4–120 through 4–123:

(1) Differential SSTL-2 outputs are only available on column clock pins.

(2) These parameters are only available on row I/O pins.

(3) SSTL-2 in maximum drive strength condition. See Table 4–101 on page 4–62 for more information on exact loading conditions for each I/O standard.

(4) SSTL-2 in minimum drive strength with $\leq$10pF output load condition.

(5) SSTL-2 in minimum drive strength with > 10pF output load condition.

(6) Differential SSTL-2 outputs are only supported on column clock pins.